

TL750L TL751L

SLVS017U-SEPTEMBER 1987-REVISED SEPTEMBER 2009

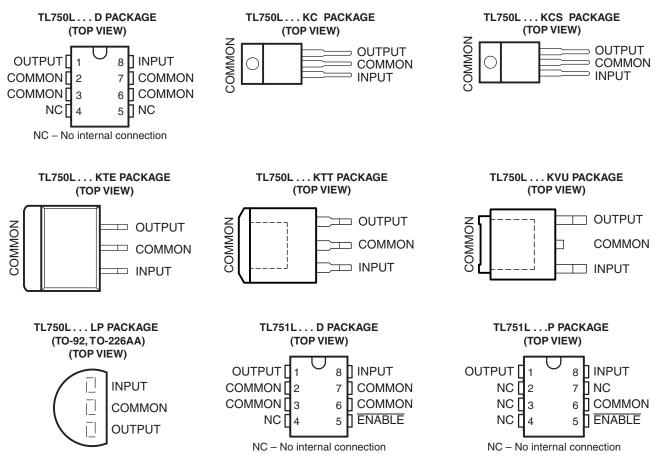
LOW-DROPOUT VOLTAGE REGULATORS

FEATURES

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- Very Low Dropout Voltage, Less Than 0.6 V at 150 mA
- Very Low Quiescent Current
- TTL- and CMOS-Compatible Enable on TL751L Series
- 60-V Load-Dump Protection

- Reverse Transient Protection Down to –50 V
- Internal Thermal-Overload Protection
- Overvoltage Protection
- Internal Overcurrent-Limiting Circuitry
- Less Than 500-µA Disable (TL751L Series)



DESCRIPTION/ORDERING INFORMATION

The TL750L and TL751L series of <u>fixed-output</u> voltage regulators offer 5-V, 8-V, 10-V, and 12-V options. The TL751L series also has an enable (ENABLE) input. When ENABLE is high, the regulator output is placed in the high-impedance state. This gives the designer complete control over power up, power down, or emergency shutdown.

The TL750L and TL751L series are low-dropout positive-voltage regulators specifically designed for battery-powered systems. These devices incorporate overvoltage and current-limiting protection circuitry, along with internal reverse-battery protection circuitry to protect the devices and the regulated system. The series is fully protected against 60-V load-dump and reverse-battery conditions. Extremely low quiescent current during full-load conditions makes these devices ideal for standby power systems.

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Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

INSTRUMENTS

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		OR	DERING INFOR	MATION ⁽¹⁾	
TJ	V _O TYP AT 25℃	PACKAG	E ⁽²⁾	ORDERABLE PART NUMBER	TOP-SIDE MARKING
		PowerFLEX [™] – KTE	Reel of 2000	TL750L05CKTER	TL750L05C
			Tube of 75	TL750L05CD	501.050
		SOIC – D	Reel of 2500	TL750L05CDR	- 50L05C
		50IC - D	Tube of 75	TL751L05CD	- 51L05C
			Reel of 2500	TL751L05CDR	511050
	5 V	TO-226/TO-92 – LP	Bulk of 1000	TL750L05CLP	7501.050
		10-220/10-92 – LP	Reel of 2000	TL750L05CLPR	- 750L05C
		TO-220 – KC	Tube of 50	TL750L05CKC	TL750L05C
		TO-220 – KCS	Tube of 50	TL750L05CKCS	TL750L05C
		TO-252 – KVU	Reel of 2500	TL750L05CKVUR	750L05C
		TO-263 – KTT	Reel of 500	TL750L05CKTTR	750L05C
		SOIC – D	Tube of 75 TL750L08CD		- 50L08C
000 40 40500	8 V	50IC - D	Reel of 2500	TL750L08CDR	- 50L08C
0°C to 125°C		TO-226/TO-92 – LP	Bulk of 1000	TL750L08CLP	750L08C
		PDIP – P	Tube of 50 TL751L10CP		TL751L10C
			Tube of 75 TL750L10CD		- 50L10C
		SOIC – D	Reel of 2500	TL750L10CDR	50L10C
	10 V	3010 - 0	Tube of 75	TL751L10CD	- 51L10C
			Reel of 2500	TL751L10CDR	511100
		TO-226/TO-92 – LP	Bulk of 1000	TL750L10CLP	- 750L10C
		10-220/10-92 - LP	Reel of 2000	TL750L10CLPR	7501100
			Tube of 75	TL750L12CD	- 50L12C
		SOIC – D	Reel of 2500	TL750L12CDR	JUL 120
	12 V	3010 - D	Tube of 75	TL751L12CD	- 51L12C
			Reel of 2500	TL751L12CDR	511120
		TO-226/TO-92 – LP	Bulk of 1000	TL750L12CLP	750L12C

For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI (1) web site at www.ti.com.

(2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

DEVICE COMPONENT	L COUNT
Transistors	20
JFETs	2
Diodes	5
Resistors	16





Absolute Maximum Ratings⁽¹⁾

over operating junction temperature range (unless otherwise noted)

			MIN	MAX	UNIT
	Continuous input voltage			26	V
	Transient input voltage ⁽²⁾	$T_A = 25^{\circ}C$		60	V
	Continuous reverse input voltage		-15	V	
	Transient reverse input voltage	t ≤ 100 ms		-50	V
TJ	Operating virtual junction temperature			150	°C
	Lead temperature	1,6 mm (1/16 in) for 10 s		260	°C
T _{stg}	Storage temperature range		-65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The transient input voltage rating applies to the waveform shown in Figure 1.

Package Thermal Data⁽¹⁾

PACKAGE	BOARD	θ _{JC}	θ _{JA}
PDIP (P)	High K, JESD 51-7	57°C/W	85°C/W
PowerFLEX™ (KTE)	High K, JESD 51-5	3°C/W	23°C/W
SOIC (D)	High K, JESD 51-7	39°C/W	97°C/W
TO-226/TO-92 (LP)	High K, JESD 51-7	55°C/W	140°C/W
TO-220 (KC)	High K, JESD 51-5	3°C/W	19°C/W
TO-220 (KCS)	High K, JESD 51-5	3°C/W	19°C/W
TO-252 (KVU)	High K, JESD 51-5	-	30.3°C/W
TO-263 (KTT)	High K, JESD 51-5	18°C/W	25.3°C/W

(1) Maximum power dissipation is a function of $T_J(max)$, θ_{JA} , and T_A . The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) - T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.

Recommended Operating Conditions

over recommended operating junction temperature range (unless otherwise noted)

				MIN	MAX	UNIT	
			TL75xL05	6	26		
V	Input voltage	TL75xL08	9	26	V		
VI	Input voltage		TL75xL10	11	26	v	
		TL75xL12	13	26			
VIH	High-level ENABLE input voltage		TL75xLxx	2	15	V	
V _{IL} ⁽¹⁾	Low-level ENABLE input voltage	$T_J = 25^{\circ}C$	TL75xLxx	-0.3	0.8	V	
VIL	LOW-level ENABLE liput voltage	$T_J = 0^{\circ}C$ to $125^{\circ}C$	TL75xLxx	-0.15	0.8	v	
I _O	Output current		TL75xLxx	0	150	mA	
TJ	Operating virtual junction temperature		TL75xLxxC	0	125	°C	

(1) <u>The algebraic convention, in which the least positive (most negative) value is designated minimum, is used in this data sheet for ENABLE voltage levels and temperature only.</u>



TL75xL05 Electrical Characteristics⁽¹⁾

 $V_1 = 14 \text{ V}, I_0 = 10 \text{ mA}, T_1 = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITI	T T		UNIT			
			MIN TYP MAX		MAX		
		$T_J = 25^{\circ}C$	4.8	5	5.2	V	
Output voltage	$V_1 = 6 V$ to 26 V, $I_0 = 0$ to 150 mA	$T_J = 0^{\circ}C$ to $125^{\circ}C$	4.75		5.25	v	
	V _I = 9 V to 16 V			5	10		
Input regulation voltage	V _I = 6 V to 26 V			6	30	mV	
Ripple rejection	V _I = 8 V to 18 V, f = 120 Hz		60	65		dB	
Output regulation voltage	I _O = 5 mA to 150 mA			20	50	mV	
Dropout voltage	I _O = 10 mA			0.2	V		
Dropout voltage	I _O = 150 mA			0.6	V		
Output noise voltage	f = 10 Hz to 100 kHz			500		μV	
	I _O = 150 mA		10	12			
Quiescent current	$V_{I} = 6 V$ to 26 V, $I_{O} = 10 \text{ mA}$, $T_{J} = 0^{\circ}C$		1	2	mA		
	ENABLE ≥ 2 V				0.5		

(1) Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1-µF capacitor across the input and a 10-µF capacitor, with equivalent series resistance of less than 0.4 Ω, across the output.

TL75xL08 Electrical Characteristics⁽¹⁾

 $V_I = 14 \text{ V}, I_O = 10 \text{ mA}, T_J = 25^{\circ}C$ (unless otherwise noted)

PARAMETER	TEST CONDITI	TI TI	UNIT					
			MIN	TYP	MAX			
Output voltogo		$T_J = 25^{\circ}C$	7.68	8	8.32	V		
Output voltage	$V_1 = 9 V$ to 26 V, $I_0 = 0$ to 150 mA	$T_J = 0^{\circ}C$ to $125^{\circ}C$	7.6		8.4	v		
	V _I = 10 V to 17 V			10	20	mV		
Input regulation voltage	V _I = 9 V to 26 V	$V_1 = 9 V$ to 26 V						
Ripple rejection	V _I = 11 V to 21 V, f = 120 Hz		60	65		dB		
Output regulation voltage	$I_0 = 5 \text{ mA to } 150 \text{ mA}$			40	80	mV		
Dropout voltage	I _O = 10 mA			0.2	V			
Dropout voltage	I _O = 150 mA			0.6	v			
Output noise voltage	f = 10 Hz to 100 kHz			500		μV		
	I _O = 150 mA		10	12				
Quiescent current	$V_{I} = 9 V$ to 26 V, $I_{O} = 10 \text{ mA}$, $T_{J} = 0^{\circ} C$	$V_{I} = 9 V$ to 26 V, $I_{O} = 10 \text{ mA}$, $T_{J} = 0^{\circ}\text{C}$ to 125°C						
	ENABLE ≥ 2 V				0.5	+		

(1) Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1-μF capacitor across the input and a 10-μF capacitor, with equivalent series resistance of less than 0.4 Ω, across the output.



TL75xL10 Electrical Characteristics⁽¹⁾

 $V_I = 14 \text{ V}, I_O = 10 \text{ mA}, T_J = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIO	TI TI	UNIT					
		MIN	TYP	MAX				
	$V_{1} = 11 V_{1}$ to 26 V/ $V_{2} = 0$ to 150 mA	$T_J = 25^{\circ}C$	9.6	10	10.4	V		
Output voltage	$V_{I} = 11 V \text{ to } 26 V, I_{O} = 0 \text{ to } 150 \text{ mA}$	$T_J = 0^{\circ}C$ to $125^{\circ}C$	9.5		10.5	v		
lanut vanulation valtana	V _I = 12 V to 19 V			10	25	mV		
Input regulation voltage	V _I = 11 V to 26 V	V _I = 11 V to 26 V						
Ripple rejection	V _I = 12 V to 22 V, f = 120 Hz		60	65		dB		
Output regulation voltage	I _O = 5 mA to 150 mA			50	100	mV		
Dronout voltage	I _O = 10 mA			0.2	V			
Dropout voltage	I _O = 150 mA	I _O = 150 mA						
Output noise voltage	f = 10 Hz to 100 kHz			700		μV		
	I _O = 150 mA		10	12				
Quiescent current	$V_I = 11$ V to 26 V, $I_O = 10$ mA, $T_J = 0^\circ$	$V_{I} = 11 \text{ V to } 26 \text{ V}, I_{O} = 10 \text{ mA}, T_{J} = 0^{\circ}\text{C to } 125^{\circ}\text{C}$						
	ENABLE ≥ 2 V				0.5			

(1) Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1-µF capacitor across the input and a 10-µF capacitor, with equivalent series resistance of less than 0.4 Ω, across the output.

TL75xL12 Electrical Characteristics⁽¹⁾

 $V_I = 14 \text{ V}, I_O = 10 \text{ mA}, T_J = 25^{\circ}C$ (unless otherwise noted)

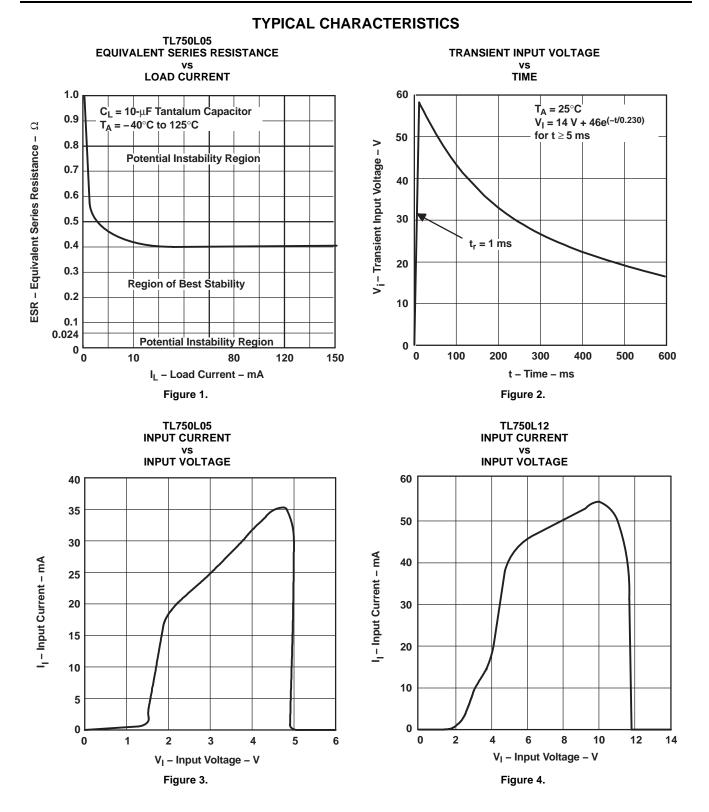
PARAMETER	TEST CONDITIO	TI TI	UNIT					
			MIN	TYP	MAX			
Output voltogo		$T_J = 25^{\circ}C$	11.52	12.48	V			
Output voltage	$V_{I} = 13 V$ to 26 V, $I_{O} = 0$ to 150 mA	$T_J = 0^{\circ}C$ to $125^{\circ}C$	11.4		12.6	v		
	V _I = 14 V to 19 V			15	30			
Input regulation voltage	V _I = 13 V to 26 V		20	40	mV			
Ripple rejection	V _I = 13 V to 23 V, f = 120 Hz		50	55		dB		
Output regulation voltage	I _O = 5 mA to 150 mA			50	120	mV		
Dranaut valtage	I _O = 10 mA			0.2	V			
Dropout voltage	I _O = 150 mA			0.6	v			
Output noise voltage	f = 10 Hz to 100 kHz			700		μV		
	I _O = 150 mA		10	12				
Quiescent current	$V_{I} = 13$ V to 26 V, $I_{O} = 10$ mA, $T_{J} = 0^{\circ}$	$V_{I} = 13 \text{ V to } 26 \text{ V}, I_{O} = 10 \text{ mA}, T_{J} = 0^{\circ}\text{C to } 125^{\circ}\text{C}$						
	ENABLE ≥ 2 V							

(1) Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1-µF capacitor across the input and a 10-µF capacitor, with equivalent series resistance of less than 0.4 Ω, across the output.

PARAMETER MEASUREMENT INFORMATION

The TL750L, TL751L series are low-dropout regulators. This means that capacitance loading is important to the performance of the regulator because it is a vital part of the control loop. The capacitor value and its equivalent series resistance (ESR) both affect the control loop and must be defined for the load range and temperature range. Figure 1 shows the recommended range of ESR for a given load with a 10-µF capacitor on the output.







PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TL750L05CD	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 125	50L05C	Samples
TL750L05CDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 125	50L05C	Samples
TL750L05CKCS	ACTIVE	TO-220	KCS	3	50	RoHS & Green	SN	N / A for Pkg Type	0 to 125	TL750L05C	Samples
TL750L05CKCSE3	ACTIVE	TO-220	KCS	3	50	RoHS & Green	SN	N / A for Pkg Type	0 to 125	TL750L05C	Samples
TL750L05CKTTR	ACTIVE	DDPAK/ TO-263	КТТ	3	500	RoHS & Green	SN	Level-3-245C-168 HR	0 to 125	TL750L05C	Samples
TL750L05CKTTRG3	ACTIVE	DDPAK/ TO-263	КТТ	3	500	RoHS & Green	SN	Level-3-245C-168 HR	0 to 125	TL750L05C	Samples
TL750L05CKVURG3	ACTIVE	TO-252	KVU	3	2500	RoHS & Green	SN	Level-3-260C-168 HR	0 to 125	750L05C	Samples
TL750L05CLP	ACTIVE	TO-92	LP	3	1000	RoHS & Green	SN	N / A for Pkg Type	0 to 125	750L05C	Samples
TL750L05CLPE3	ACTIVE	TO-92	LP	3	1000	RoHS & Green	SN	N / A for Pkg Type	0 to 125	750L05C	Samples
TL750L05CLPR	ACTIVE	TO-92	LP	3	2000	RoHS & Green	SN	N / A for Pkg Type	0 to 125	750L05C	Samples
TL750L05CLPRE3	ACTIVE	TO-92	LP	3	2000	RoHS & Green	SN	N / A for Pkg Type	0 to 125	750L05C	Samples
TL750L08CD	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	0 to 125	50L08C	Samples
TL750L08CDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	0 to 125	50L08C	Samples
TL750L08CLP	ACTIVE	TO-92	LP	3	1000	RoHS & Green	SN	N / A for Pkg Type	0 to 125	750L08C	Samples
TL750L08CLPE3	ACTIVE	TO-92	LP	3	1000	RoHS & Green	SN	N / A for Pkg Type	0 to 125	750L08C	Samples
TL750L10CD	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 125	50L10C	Samples
TL750L10CDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 125	50L10C	Samples
TL750L10CLP	ACTIVE	TO-92	LP	3	1000	RoHS & Green	SN	N / A for Pkg Type	0 to 125	750L10C	Samples
TL750L10CLPR	ACTIVE	TO-92	LP	3	2000	RoHS & Green	SN	N / A for Pkg Type	0 to 125	750L10C	Samples



Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
TL750L12CD	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 125	50L12C	Samples
TL750L12CDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 125	50L12C	Samples
TL750L12CLP	ACTIVE	TO-92	LP	3	1000	RoHS & Green	SN	N / A for Pkg Type	0 to 125	750L12C	Samples
TL751L05CD	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 125	51L05C	Samples
TL751L05CDE4	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 125	51L05C	Samples
TL751L05CDG4	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 125	51L05C	Samples
TL751L05CDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 125	51L05C	Samples
TL751L10CD	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 125	51L10C	Samples
TL751L10CDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 125	51L10C	Samples
TL751L10CP	ACTIVE	PDIP	Р	8	50	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 125	TL751L10C	Samples
TL751L12CD	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 125	51L12C	Samples
TL751L12CDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 125	51L12C	Samples
TL751L12CDRG4	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 125	51L12C	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ **RoHS**: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.



PACKAGE OPTION ADDENDUM

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TEXAS

STRUMENTS

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TL750L05CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL750L05CKTTR	DDPAK/ TO-263	КТТ	3	500	330.0	24.4	10.8	16.3	5.11	16.0	24.0	Q2
TL750L05CKVURG3	TO-252	KVU	3	2500	330.0	16.4	6.9	10.5	2.7	8.0	16.0	Q2
TL750L08CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL750L10CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL750L12CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL751L05CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL751L10CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL751L12CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1



PACKAGE MATERIALS INFORMATION

25-Sep-2024



Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)					
TL750L05CDR	SOIC	D	8	2500	353.0	353.0	32.0					
TL750L05CKTTR	DDPAK/TO-263	ктт	3	500	340.0	340.0	38.0					
TL750L05CKVURG3	TO-252	KVU	3	2500	340.0	340.0	38.0					
TL750L08CDR	SOIC	D	8	2500	340.5	338.1	25.0					
TL750L10CDR	SOIC	D	8	2500	340.5	338.1	20.6					
TL750L12CDR	SOIC	D	8	2500	353.0	353.0	32.0					
TL751L05CDR	SOIC	D	8	2500	340.5	338.1	20.6					
TL751L10CDR	SOIC	D	8	2500	340.5	338.1	20.6					
TL751L12CDR	SOIC	D	8	2500	340.5	338.1	20.6					

TEXAS INSTRUMENTS

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25-Sep-2024

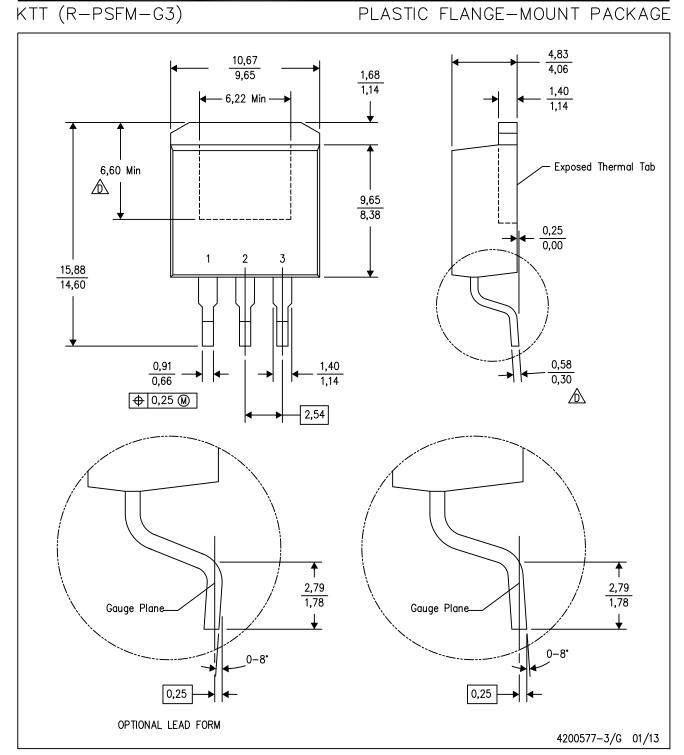
TUBE



- B - Alignment groove width

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
TL750L05CD	D	SOIC	8	75	507	8	3940	4.32
TL750L05CKCS	KCS	TO-220	3	50	532	34.1	700	9.6
TL750L05CKCSE3	KCS	TO-220	3	50	532	34.1	700	9.6
TL750L08CD	D	SOIC	8	75	507	8	3940	4.32
TL750L10CD	D	SOIC	8	75	507	8	3940	4.32
TL750L12CD	D	SOIC	8	75	507	8	3940	4.32
TL751L05CD	D	SOIC	8	75	507	8	3940	4.32
TL751L05CDE4	D	SOIC	8	75	507	8	3940	4.32
TL751L05CDG4	D	SOIC	8	75	507	8	3940	4.32
TL751L10CD	D	SOIC	8	75	507	8	3940	4.32
TL751L10CP	Р	PDIP	8	50	506	13.97	11230	4.32
TL751L12CD	D	SOIC	8	75	507	8	3940	4.32

MECHANICAL DATA



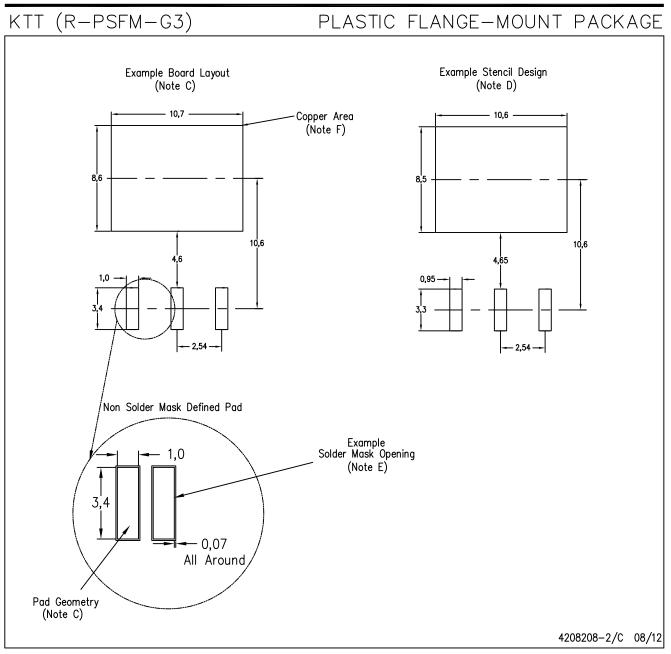
NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion. Mold flash or protrusion not to exceed 0.005 (0,13) per side.

A Falls within JEDEC TO-263 variation AA, except minimum lead thickness and minimum exposed pad length.





NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-SM-782 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.
- F. This package is designed to be soldered to a thermal pad on the board. Refer to the Product Datasheet for specific thermal information, via requirements, and recommended thermal pad size. For thermal pad sizes larger than shown a solder mask defined pad is recommended in order to maintain the solderable pad geometry while increasing copper area.



D0008A



PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.

- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



D0008A

EXAMPLE BOARD LAYOUT

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



D0008A

EXAMPLE STENCIL DESIGN

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



P(R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.



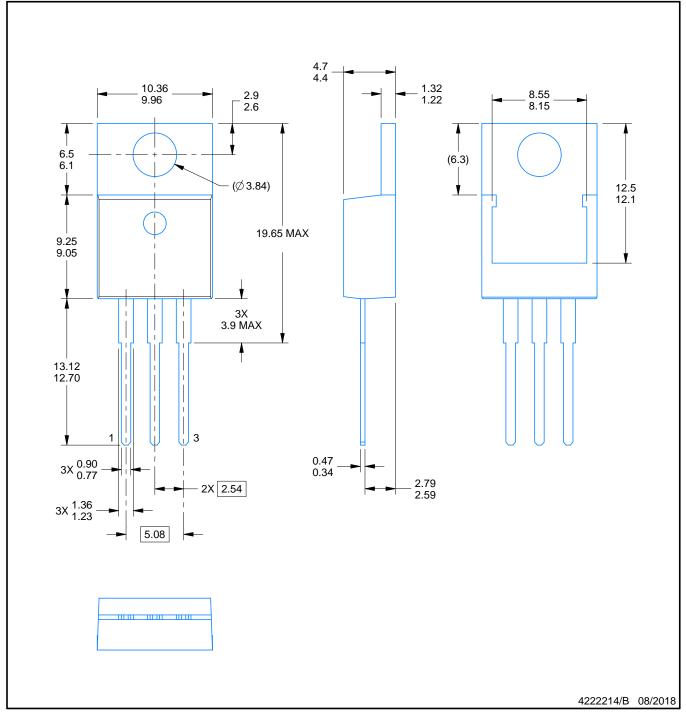
KCS0003B



PACKAGE OUTLINE

TO-220 - 19.65 mm max height

TO-220



NOTES:

- 1. Dimensions are in millimeters. Any dimension in brackets or parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 Reference JEDEC registration TO-220.

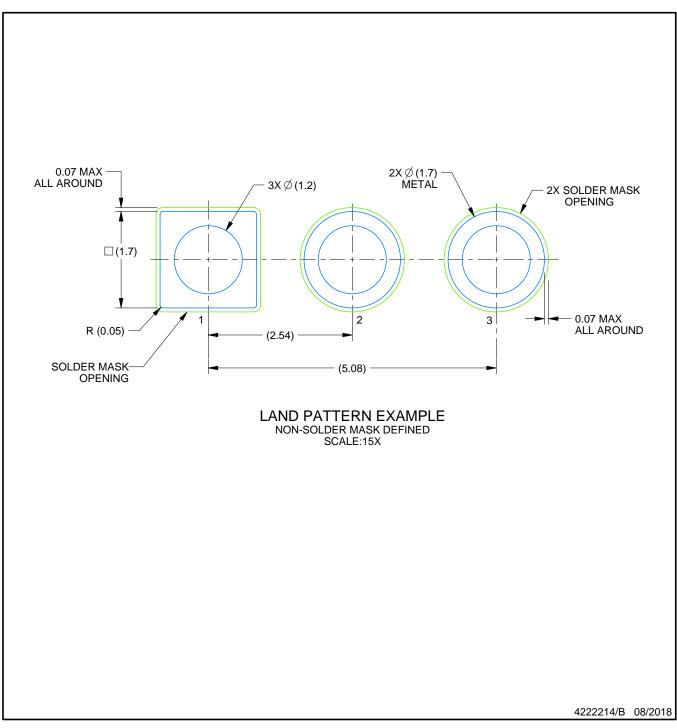


KCS0003B

EXAMPLE BOARD LAYOUT

TO-220 - 19.65 mm max height

TO-220





GENERIC PACKAGE VIEW

TO-92 - 5.34 mm max height TRANSISTOR OUTLINE



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



LP0003A



PACKAGE OUTLINE

TO-92 - 5.34 mm max height

TO-92



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice.
- Lead dimensions are not controlled within this area.
 Reference JEDEC TO-226, variation AA.
- 5. Shipping method:

 - a. Straight lead option available in bulk pack only.b. Formed lead option available in tape and reel or ammo pack.
 - c. Specific products can be offered in limited combinations of shipping medium and lead options.
 - d. Consult product folder for more information on available options.

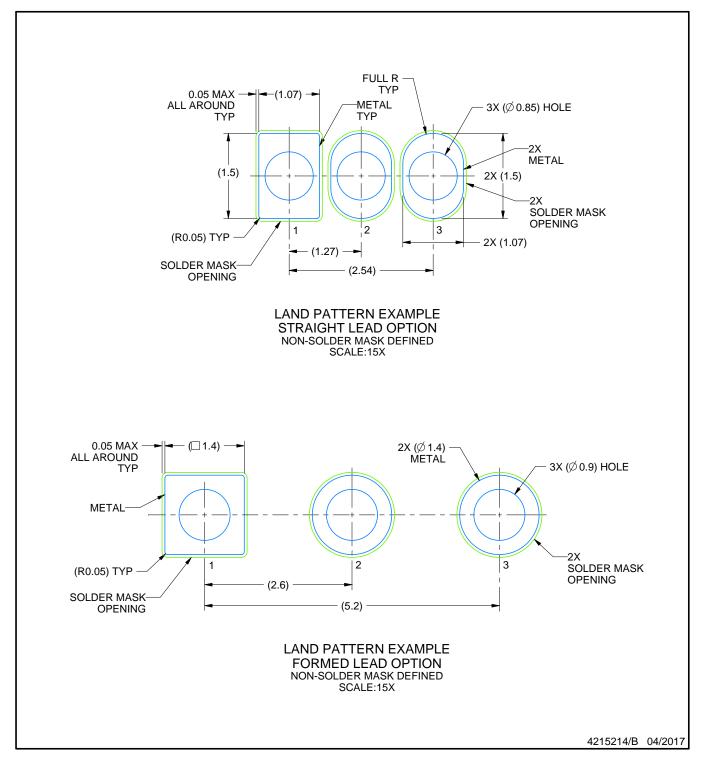


LP0003A

EXAMPLE BOARD LAYOUT

TO-92 - 5.34 mm max height

TO-92





LP0003A

TAPE SPECIFICATIONS

TO-92 - 5.34 mm max height

TO-92

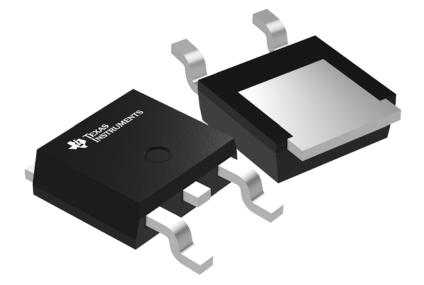




KVU 3

GENERIC PACKAGE VIEW

TO-252 - 2.52 mm max height TRANSISTOR OUTLINE



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



4205521-2/E

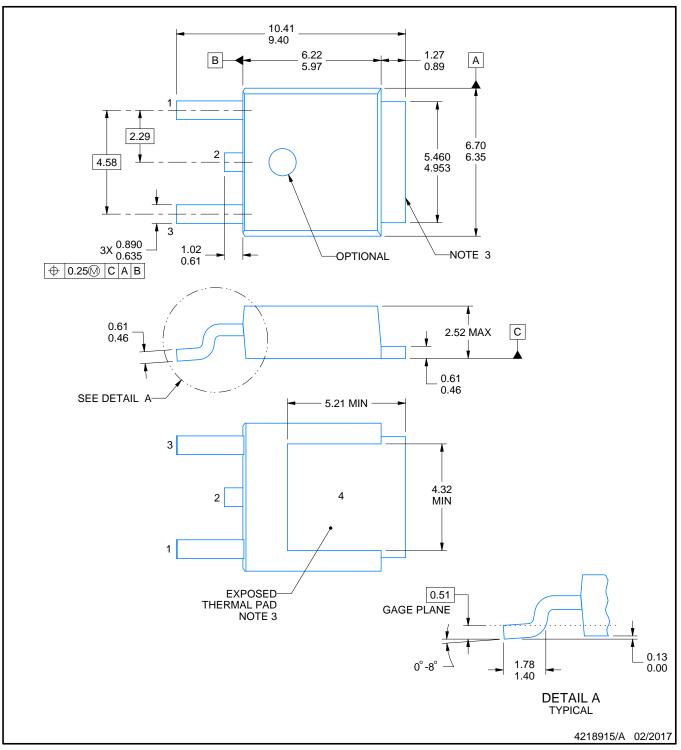
KVU0003A



PACKAGE OUTLINE

TO-252 - 2.52 mm max height

TO-252



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 Shape may vary per different assembly sites.
 Reference JEDEC registration TO-252.

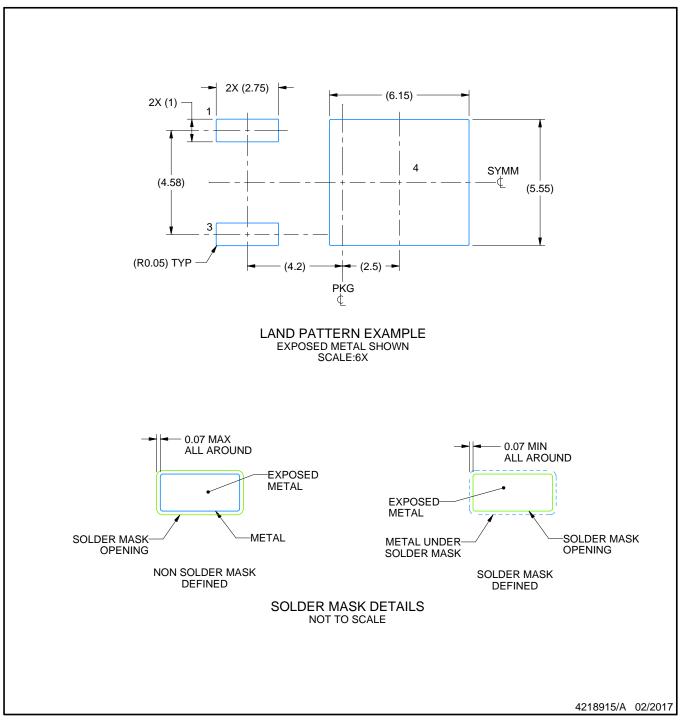


KVU0003A

EXAMPLE BOARD LAYOUT

TO-252 - 2.52 mm max height

TO-252



NOTES: (continued)

5. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature numbers SLMA002(www.ti.com/lit/slm002) and SLMA004 (www.ti.com/lit/slma004).

6. Vias are optional depending on application, refer to device data sheet. It is recommended that vias under paste be filled, plugged or tented.

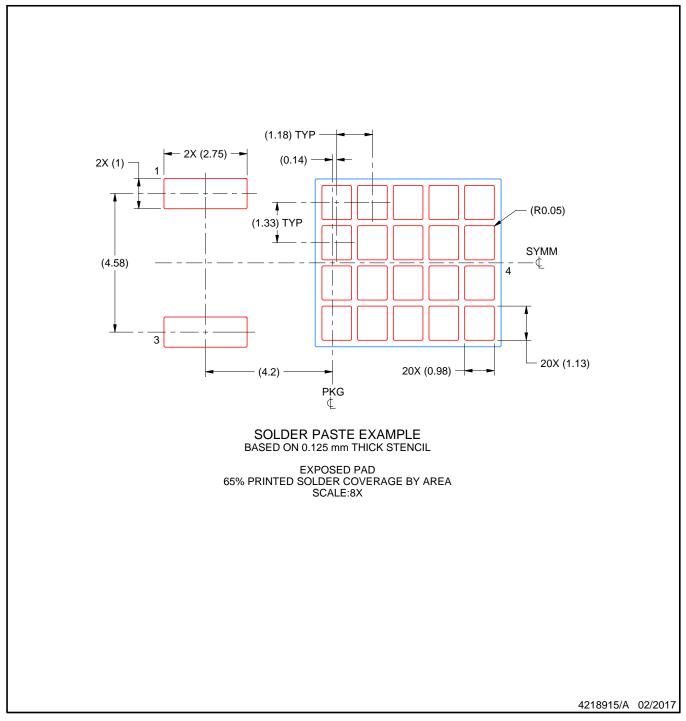


KVU0003A

EXAMPLE STENCIL DESIGN

TO-252 - 2.52 mm max height

TO-252



NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations. 8. Board assembly site may have different recommendations for stencil design.



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